

L-Band, GaN/SiC, RF Power Transistor

1.2 - 1.4 GHz | 650 W typ | 70% Efficiency typ | 15 dB Gain typ | 50 V | 2ms Pulse Length, 20% Duty Cycle

IGN1214L500B is a high power GaN-on-SiC RF power transistor that has been designed to suit the unique needs of modern long-pulse, long-range radar systems. It supplies a minimum of 500 W of peak output power, with typically >15 dB of gain and 70% efficiency. It operates from a 50 V supply voltage. For optimal thermal efficiency, the transistor is housed in a metal-based package with an epoxysealed ceramic lid.

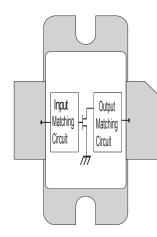
FEATURES

- GaN on SiC HEMT Technology
- Output Power >500 W
- Pre-matched Input and Output Impedance
- High Efficiency up to 75%
- 100% RF Tested Under 2ms, 20% duty cycle pulse conditions
- RoHS and REACH Compliant

APPLICATIONS

L-band Radar Systems





Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V _{DS}	160	V	25 °C
DC Gate-Source Voltage	V _{GS}	-8 to +1.5	V	25 °C
DC Drain Current	I _D	48	А	25 °C
DC Gate Current	Ι _G	4.8	mA	25 °C
RF Input Power	P _{rein}	25	W	25 °C
Operating Junction Temperature	T,	-55 to +200	٥C	
Storage Temperature	T _{stg}	-55 to +150	٥C	
Soldering Temperature	T _{SOLDER}	260 for 60s	٥C	

Table 1. Absolute Maximum Ratings (Not Simultaneous)

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Мах	Units	Test Conditions
Gate Pinch-Off Voltage	V _P	-5.0			V	$V_{_{\rm DS}} = 50$ V, $I_{_{\rm DS}} = 1$ mA
Quiescent Gate Voltage	V _Q		-2.6		V	$V_{_{\rm DS}} = 50V, I_{_{\rm DS}} = 200 {\rm mA}$



Table 3. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Input Return Loss	IRL	18	15	7	dB	P _{out} = 500W
RF Input Power	P _{IN, RF}	11.2	16.0	17.5	W	f = 1.2, 1.3, 1.4 GHz
Gain	G	14.5	15.0	16.5	dB	
Drain Efficiency	η	52	65	75	%	2ms pulse length 20% duty cycle pulse conditions
Pulse Droop	D	-0.8	-0.4	+0.1	dB	$\lambda = 50 \lambda = 200 \text{ m}$
Load Mismatch Stability	VSWR-S	2:1				$V_{\rm DS} = 50$ V, $I_{\rm DS} = 200$ mA,
VSWR Withstand	VSWR-LMT	3:1				

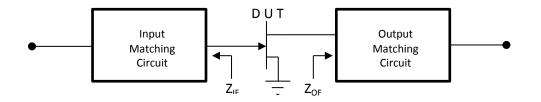
Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 4. Thermal Resistance (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Peak Thermal Resistance, Junction to Case	R _{TH(JC)}		TBD		°C/W	$\begin{array}{l} P_{out}=500W\\ f=1.2, 1.3, 1.4~GHz\\ 2ms~pulse~length, 20\%~duty~cycle\\ V_{DS}=50V, I_{DS}=200mA \end{array}$

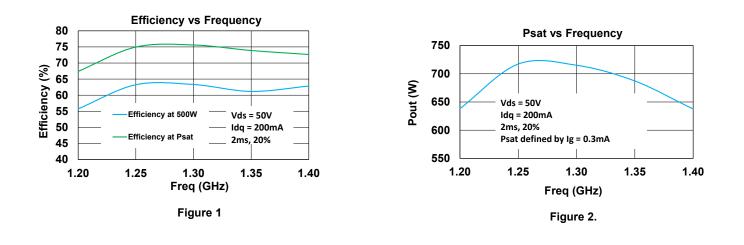
Table 5. Optimum Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

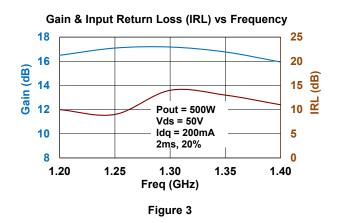
Frequency (GHz)	Z _{IF}	Z _{of}	Units	Test Conditions
1.2	1.8 - j 1.1	2.0 - j 1.8	Ω	P _{out} = 500W
1.3	2.0 - j 0.3	2.0 - j 1.6	Ω	2ms Pulse length, 20% Duty Cycle $V_{_{\rm DS}}=50 \text{V}, \text{I}_{_{\rm DS}}=200 \text{mA}$
1.4	2.3 + j 0.4	1.9 - j 1.4	Ω	

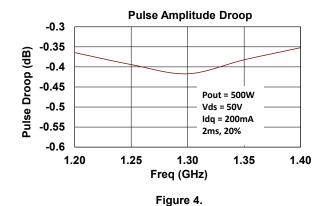




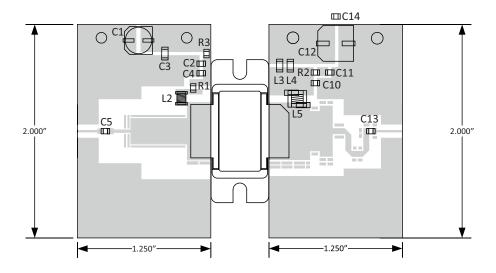
TYPICAL PERFORMANCE









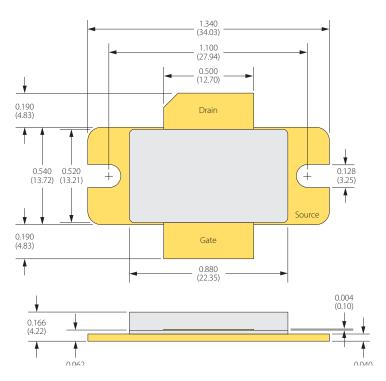


TEST FIXTURE

Bill of Materials for IGN1214L500B Test Fixture

Designator	Description	Quantity	Part Number	
C1	CAP 47μF, 25V	1	AIEI	
C2	CAP 1µF, 1206, 100V	1		
C3 ,C11	CAP 0.1µF, 0805, 50V	2		
C5, C13	CAP 18pF, Edge Mount	CAP 18pF, Edge Mount 2 ATC600F180		
C4, C10	CAP 18pF 2 ATC600F180		ATC600F180	
C12	САР 68µF, 0810, 63V	1	AIEI	
C14	CAP, 4700µF, 63V (mounted external to pcb)	1		
L2	IND 27.3nH, 0908SQ-27N 1 CC		СС	
L3, L4	IND FB, 33 OHM, 1206, 6A	2	Murata BLM31PG330SN1L	
L5	IND, 18.5nH	1	CC A05T_L_J	
R1, R2	RES, 10 OHM, 0805	2		
R3	RES, 200 OHM, 0805	1		
PC Board Type	ROGERS RT6110.2, 25mil, 1/1oz. Copper	2		





PACKAGE PL95A1

Dimensions: Inches (mm)



ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivty Level (MSL)	0	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- •Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- •Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

DEFINITIONS

DATA SHEET STATUS

arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale. Copyright © 2018.

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Advanced Specification - This data sheet contains Advanced specifications. Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability. DISCLAIMER: Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability